3.3 V/5 V ECL \div 2 Divider

MC10EP32, MC100EP32

Description

The MC10/100EP32 is an integrated $\div 2$ divider with differential CLK inputs.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μF capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

The reset pin is asynchronous and is asserted on the rising edge. Upon power-up, the internal flip-flops will attain a random state; the reset allows for the synchronization of multiple EP32's in a system.

The 100 Series contains temperature compensation.

Features

- 350 ps Typical Propagation Delay
- Maximum Frequency > 4 GHz Typical (Figure 3)
- PECL Mode Operating Range:
 - $V_{CC} = 3.0 \text{ V}$ to 5.5 V with $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:
 - $V_{CC} = 0 \text{ V}$ with $V_{EE} = -3.0 \text{ V}$ to -5.5 V
- Open Input Default State
- Safety Clamp on Inputs
- Q Output Will Default LOW with Inputs Open or at V_{EE}
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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SOIC-8 NB D SUFFIX

TSSOP-8 **DT SUFFIX** CASE 751-07 CASE 948R-02

DFN_8 **MN SUFFIX** CASE 506AA

MARKING DIAGRAMS*











= MC10 Н

Α = Assembly Location

= MC100 3K = MC100 = Wafer Lot = Year

= Date Code

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

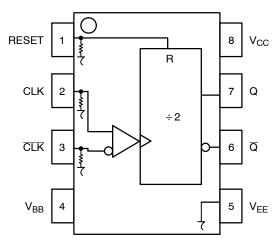


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

Pin	Function
CLK, CLK*	ECL Clock Inputs
Reset*	ECL Asynchronous Reset
V _{BB}	Reference Voltage Output
Q, Q	ECL Data Outputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply
EP	(DFN-8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave uncon- nected, floating open.

^{*}Pins will default LOW when left open.

Table 2. TRUTH TABLE

CLK	CLK	RESET	Q	Q
X	X	Z	L	H
Z	Z	L	F	F

 \overline{Z} = LOW to HIGH Transition \overline{Z} = HIGH to LOW Transition F = Divide by 2 Function

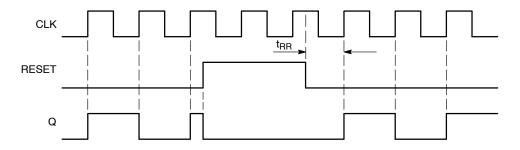


Figure 2. Timing Diagram

Table 3. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	78 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

^{1.} For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V _{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$V_{I} \leq V_{CC}$ $V_{I} \geq V_{EE}$	6 -6	٧
l _{out}	Output Current	Continuous Surge		50 100	mA
I _{BB}	V _{BB} Sink/Source			±0.5	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8	129 84	°C/W
θЈС	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN8	35 to 40	°C/W
T _{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 5. 10EP DC CHARACTERISTICS, PECL ($V_{CC} = 3.3 \text{ V}, V_{EE} = 0 \text{ V}$ (Note 1))

		-40°C		25°C							
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	40	23	30	40	23	30	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V _{OL}	Output LOW Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2090		2415	2155		2480	2215		2540	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1365		1690	1430		1755	1490		1815	mV
V _{BB}	Output Voltage Reference	1790	1890	1990	1855	1955	2055	1915	2015	2115	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	٧
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to -2.2 V.
 All loading with 50 Ω to V_{CC} 2.0 V.
 V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

^{1.} JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 6. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	40	23	30	40	23	30	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	3865	3990	4115	3930	4055	4180	3990	4115	4240	mV
V _{OL}	Output LOW Voltage (Note 2)	3065	3190	3315	3130	3255	3380	3190	3315	3440	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3790		4115	3855		4180	3915		4240	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3065		3390	3130		3455	3190		3515	mV
V_{BB}	Output Voltage Reference	3490	3590	3690	3555	3655	3755	3615	3715	3815	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μА

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +2.0 V to -0.5 V.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. 10EP DC CHARACTERISTICS, NECL ($V_{CC} = 0 \text{ V}$; $V_{EE} = -5.5 \text{ V}$ to -3.0 V (Note 1))

			−40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	40	23	30	40	23	30	40	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV
V _{OL}	Output LOW Voltage (Note 2)	-1935	-1810	-1685	-1870	-1745	-1620	-1810	-1685	-1560	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1210		-885	-1145		-820	-1085		-760	mV
V_{IL}	Input LOW Voltage (Single-Ended)	-1935		-1610	-1870		-1545	-1810		-1485	mV
V_{BB}	Output Voltage Reference	-1510	-1410	-1310	-1445	-1345	-1245	-1385	-1285	-1185	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V _{EE}	+2.0	0.0	V _{EE}	+2.0	0.0	V _{EE}	+2.0	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC}.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 8. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	37	26	34	40	28	36	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V _{BB}	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -2.2 V.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- 3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 9. 100EP DC CHARACTERISTICS, PECL ($V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$ (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	37	26	34	40	28	36	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V _{OL}	Output LOW Voltage (Note 2)	3055	3180	3305	3055	3180	3305	3055	3180	3305	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
V_{BB}	Output Voltage Reference	3475	3575	3675	3475	3575	3675	3475	3575	3675	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +2.0 V to -0.5 V.
- All loading with 50 Ω to V_{CC} 2.0 V.
 V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 10. 100EP DC CHARACTERISTICS, NECL ($V_{CC} = 0 \text{ V}$; $V_{EE} = -5.5 \text{ V}$ to -3.0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	23	30	37	26	34	40	28	36	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
V _{BB}	Output Voltage Reference	-1525	-1425	-1325	-1525	-1425	-1325	-1525	-1425	-1325	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V _{EE}	+2.0	0.0	V _{EE}	+2.0	0.0	V _{EE}	+2.0	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 1. Input and output parameters vary 1:1 with V_{CC}.
- 2. All loading with 50 Ω to V_{CC} 2.0 V.
- V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

 $\textbf{Table 11. AC CHARACTERISTICS} \ (V_{CC} = 0 \ V; \ V_{EE} = -3.0 \ V \ to \ -5.5 \ V \ \ or \ \ V_{CC} = 3.0 \ V \ to \ 5.5 \ V; \ V_{EE} = 0 \ V \ (Note \ 1))$

			-40°C			25°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{OPP}	Output Voltage Amplitude (See Figure 3) f _{in} < 3.5 GHz f _{in} @ 4.0 GHz	640	700 740		630	700 710		500	700 600		mV
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential CLK to Q, Q 10 Series RESET to Q, Q 100 Series RESET to Q, Q	250 220 320	330 290 400	420 390 480	270 250 320	350 300 400	450 390 480	320 320 375	400 380 450	480 460 525	ps
t _{RR}	Set/Reset Recovery	200	175		200	175		200	175		ps
t _{PW}	Minimum Pulse width RESET	550	475		550	475		550	475		ps
UITTER	CLOCK Random Jitter (RMS) f _{in} < 3.5 GHz f _{in} @ ≤ 4.0 GHz		0.5 0.5	1.5		0.5 0.5	1.5		0.5 0.5	1.5	ps
V _{PP}	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t _r	Output Rise/Fall Times Q, Q (20% - 80%)	50	100	150	70	120	170	70	130	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

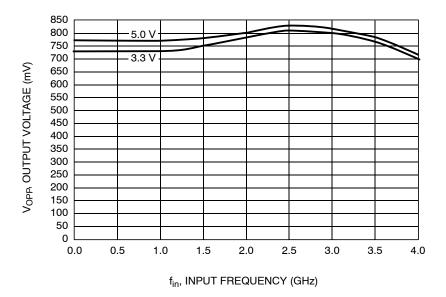


Figure 3. Input Frequency (f_{in}) Versus Typical Output Voltage (V_{OPP})

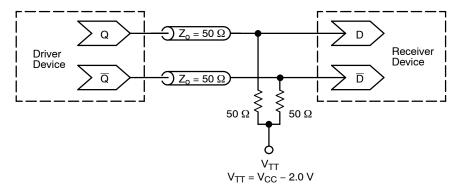


Figure 4. Typical Termination for Output Driver and Device Evaluation (See Application Note $\underline{\text{AND8020/D}}$ – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10EP32DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC10EP32DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC10EP32DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC10EP32DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100EP32DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EP32DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC100EP32DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EP32DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel
MC100EP32MNR4G	DFN-8 (Pb-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D - The ECL Translator Guide

AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices

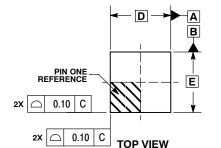
ECLinPS is a trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

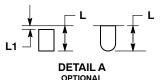


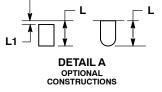


DFN8 2x2, 0.5P CASE 506AA **ISSUE F**

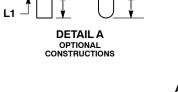
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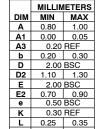




EXPOSED Cu



MOLD CMPD

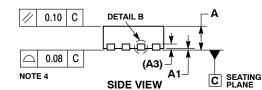


DIMENSIONING AND TOLERANCING PER

PAD AS WELL AS THE TERMINALS.

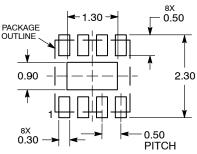
ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED

NOTES

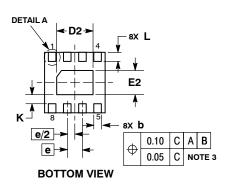


DETAIL B ALTERNATE CONSTRUCTIONS

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS



GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Device

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBE		98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
	DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITCH		PAGE 1 OF 1

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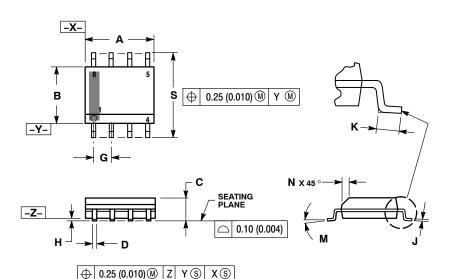
^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.





SOIC-8 NB CASE 751-07 **ISSUE AK**

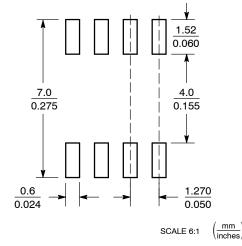
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- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

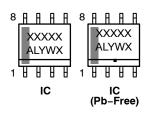
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package

XXXXXX = Specific Device Code = Assembly Location Α = Year ww = Work Week = Pb-Free Package

XXXXXX

AYWW

Discrete

Ŧ \mathbb{H} AYWW

Discrete (Pb-Free)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	PIN 1. COLLECTOR, DIE #1 2. BASE, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 9. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN
3. V10UT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22:	7. DRAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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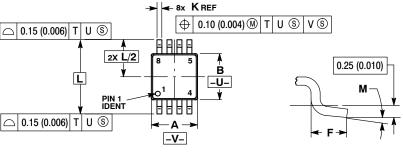


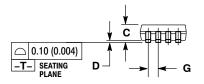


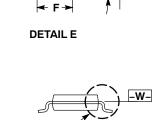
TSSOP 8 CASE 948R-02 ISSUE A

DATE 04/07/2000

SCALE 2:1







DETAIL E

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193	BSC
М	0°	6 °	0°	6°

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